

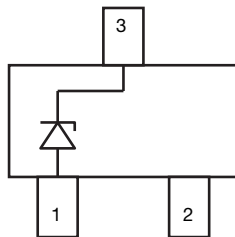
Description

The DCSOT12N is an uni-directional TVS diode leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The DCSOT12N complies with the IEC 61000-4-2 (ESD) standard with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a lead-free SOT-23 package. It is designed to protect components which are connected to data and transmission lines from voltage surges.

Mechanical Characteristics

- ◆ Package: SOT-23
- ◆ Lead Finish: Matte Tin
- ◆ Case Material: "Green" Molding Compound.
- ◆ Moisture Sensitivity: Level 3 per J-STD-020
- ◆ Terminal Connections: See Diagram Below
- ◆ Marking Information: See Below

Dimensions and Pin Configuration



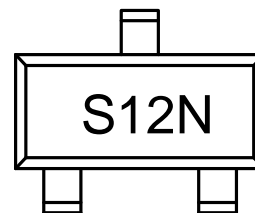
Features

- ◆ 350W peak pulse power(8/20 μs)
- ◆ Protects two uni-directional lines
- ◆ Ultra low leakage: nA level
- ◆ Operating voltage: 12V
- ◆ Low clamping voltage
- ◆ Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lighting) 13A (8/20 μs)
- ◆ RoHS Compliant

Applications

- ◆ Cellular Handsets and Accessories
- ◆ Notebook and Handhelds
- ◆ Portable Instrumentation
- ◆ Set Top Box
- ◆ Industrial Controls
- ◆ Server and Desktop PC

Marking Information



Marking Code

Ordering Information

Part Number	Marking	Packaging	Reel Size
DCSOT12N	S12N	3000/Tape & Reel	7 inch

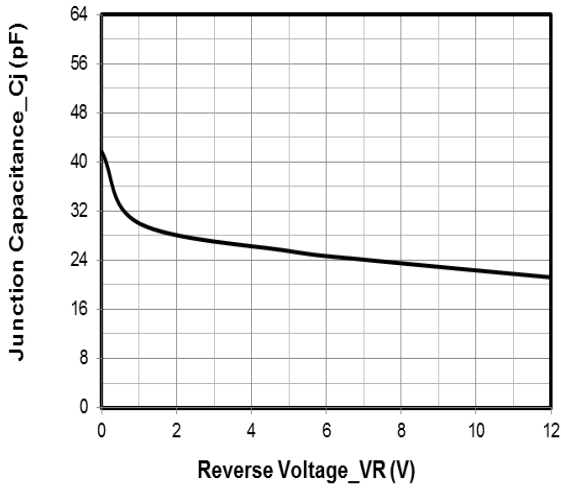
Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	350	W
Peak Pulse Current (8/20 μs)	I _{PP}	13	A
ESD per IEC 61000-4-2 (Air)	VESD	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	
Operating Temperature Range	T _J	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	T _{stg}	-55 to +150	$^\circ\text{C}$

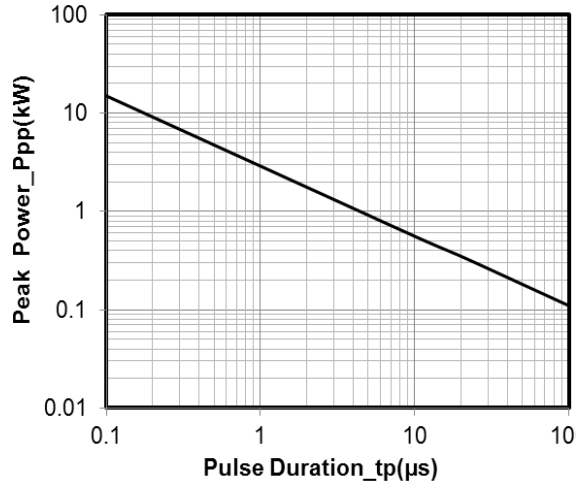
Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			12	V	
Breakdown Voltage	V _{BR}	13.3			V	I _T = 1mA
Reverse Leakage Current	I _R			0.2	μA	V _{RWM} = 12V
Clamping Voltage	V _C			16	V	I _{PP} = 1A (8 x 20 μs pulse)
Clamping Voltage	V _C		24	27	V	I _{PP} = 13A (8 x 20 μs pulse)
Junction Capacitance	C _J		40		pF	V _R = 0V, f = 1MHz, Pin 1 to Pin 3

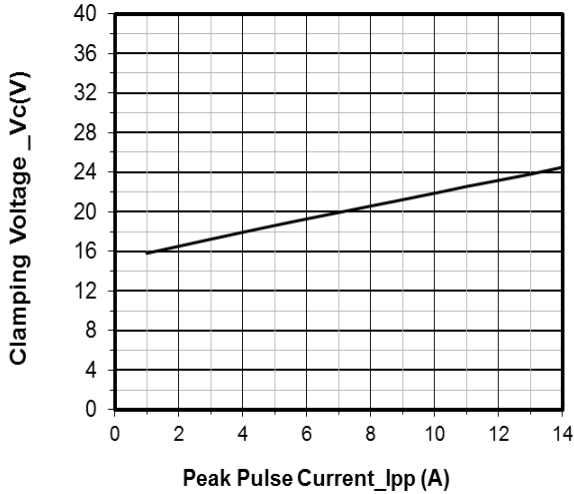
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



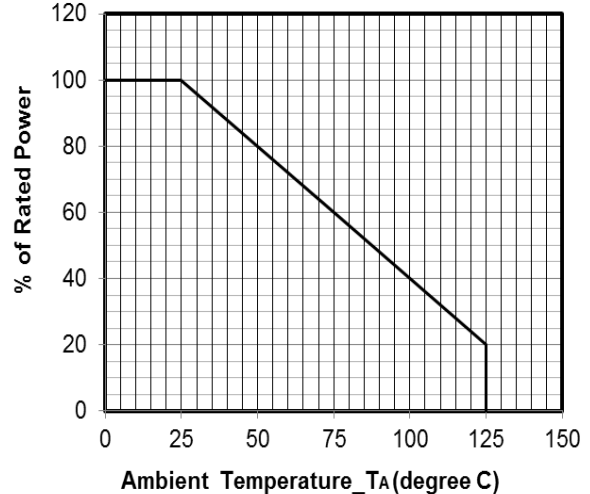
Junction Capacitance vs. Reverse Voltage



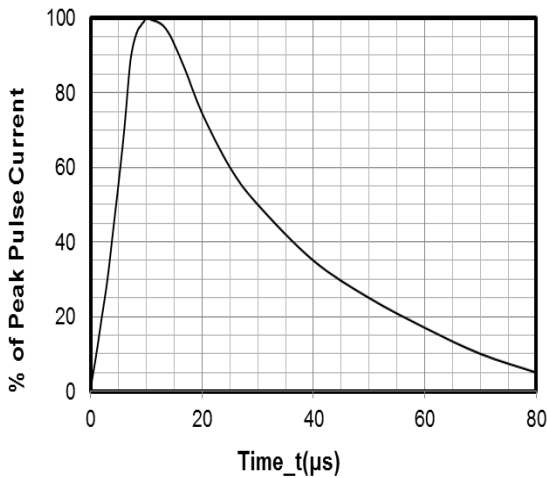
Peak Pulse Power vs. Pulse Time



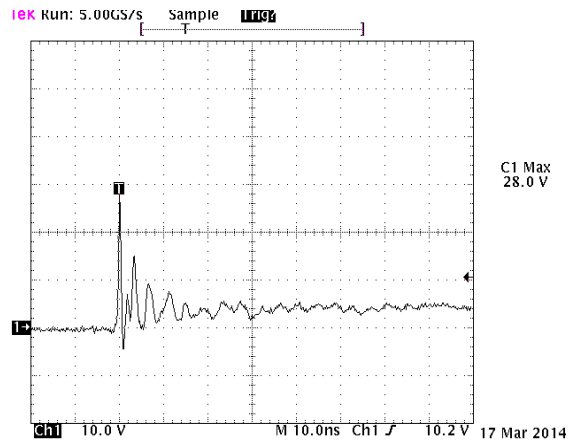
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



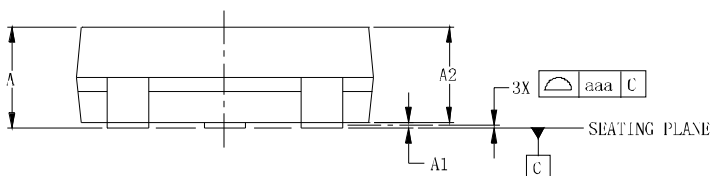
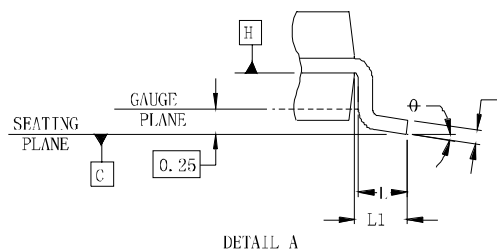
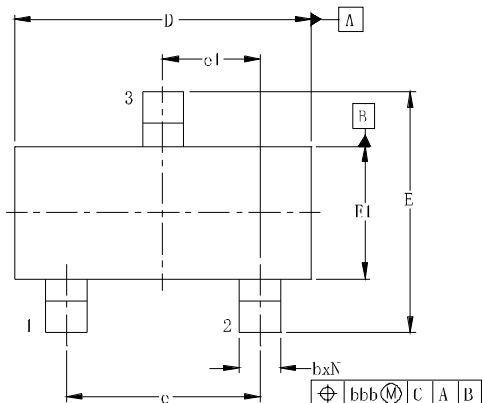
8 X 20μs Pulse Waveform



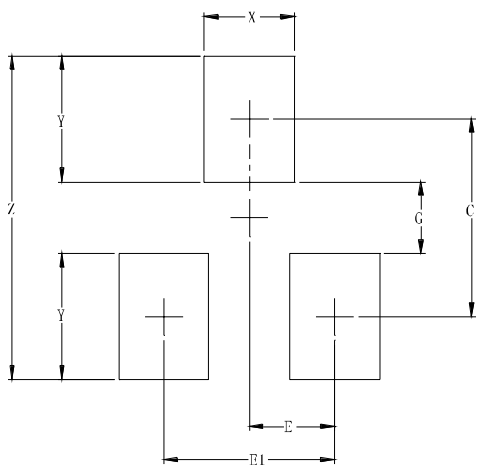
Note: Data is taken with a 10x attenuator

**ESD Clamping Voltage
8 kV Contact per IEC61000-4-2**

SOT-23 Package Outline Drawing



Suggested Land Pattern



DIMENSIONS						
SYM	INCHES			MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.035	-	0.044	0.89	-	1.12
A1	0.000	-	0.004	0.01	-	0.10
A2	0.035	0.037	0.040	0.88	0.95	1.02
b	0.012	-	0.020	0.30	-	0.51
c	0.003	-	0.007	0.08	-	0.18
D	0.110	0.114	0.120	2.80	2.90	3.04
E	0.082	0.093	0.104	2.10	2.37	2.64
E1	0.047	0.051	0.055	1.20	1.30	1.40
e	0.075			1.90BSC		
e1	0.037			0.95BSC		
L	0.015	0.020	0.024	0.40	0.50	0.60
L1	0.022			0.55		
N	3			3		
ϕ	0°	-	8°	0°	-	8°
aaa	0.004			0.10		
bbb	0.008			0.20		

DIMENSIONS		
SYM	INCHES	MILLIMETERS
C	0.087	2.20
E	0.037	0.95
E1	0.075	1.90
G	0.031	0.80
X	0.039	1.00
Y	0.055	1.40
Z	0.141	3.60

Contact Information

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